

# Ángel G Rodríguez

## List of Publications by Year in descending order

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docs citations

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1137  
citing authors

#	ARTICLE	IF	CITATIONS
1	Raman Spectroscopy of Individual Cervical Exfoliated Cells in Premalignant and Malignant Lesions. Applied Sciences (Switzerland), 2022, 12, 2419.	2.5	3
2	Thermal tuning of the morphology of hydrothermally synthesized CeO <sub>2</sub> nanotubes for photocatalytic applications. Ceramics International, 2022, 48, 17802-17815.	4.8	4
3	Strain and annealing temperature effects on the optical properties of GaNAs layers grown by molecular beam epitaxy. Thin Solid Films, 2022, 748, 139147.	1.8	2
4	Relating the Synthesis Method of VOX/CeO <sub>2</sub> /SiO <sub>2</sub> Catalysts to Red-Ox Properties, Acid Sites, and Catalytic Activity for the Oxidative Dehydrogenation of Propane and n-Butane. Topics in Catalysis, 2022, 65, 1408-1418.	2.8	2
5	Structural and Raman study of the thermoelectric solid solution Sr <sub>1.9</sub> La <sub>0.1</sub> Nb <sub>2</sub> O <sub>7</sub> . Journal of Raman Spectroscopy, 2021, 52, 737-749.	2.5	1
6	Low concentration (x <math>\leq 0.01</math>) Gd doping of CeO <sub>2</sub> thin films for n-type layers deposited by spin coating. Thin Solid Films, 2021, 724, 138602.	1.8	6
7	One-pot hydrothermal synthesis and formation mechanism of SrNb <sub>2</sub> O <sub>6</sub> â€“Sr <sub>2</sub> Nb <sub>2</sub> O <sub>7</sub> â€“Sr <sub>5</sub> Nb <sub>4</sub> O <sub>15</sub> lamellar perovskites in highly concentrated NaOH solutions. Ceramics International, 2021, 47, 25622-25633.	4.8	5
8	Structure, Acidity, and Redox Aspects of VOx/ZrO <sub>2</sub> /SiO <sub>2</sub> Catalysts for the n-Butane Oxidative Dehydrogenation. Catalysts, 2020, 10, 550.	3.5	4
9	Overlapping effects of the optical transitions of GaNAs thin films grown by molecular beam epitaxy. Thin Solid Films, 2020, 702, 137969.	1.8	4
10	High-pressure structural change in the ferroelectric layered perovskite $Sr_{1-x}Nb_2O_7$ . CrystEngComm, 2019, 19, 3451-3459.	3.2	8
11	Orthorhombic distortion in Au nanoparticles induced by high pressure. CrystEngComm, 2019, 21, 3451-3459.	2.6	7
12	Hydrazine-free chemical bath deposition of WSe <sub>2</sub> thin films and bi-layers for photovoltaic applications. Materials Research Express, 2019, 6, 105906.	1.6	2
13	Effects of Mg incorporation in cubic GaN films grown by PAMBE near Ga rich conditions. Materials Science in Semiconductor Processing, 2019, 93, 196-200.	4.0	8
14	Temperature dependence of the Raman dispersion of Sr <sub>2</sub> Nb <sub>2</sub> O <sub>7</sub> : Influence of an electric field during the synthesis. Journal of Raman Spectroscopy, 2019, 50, 102-114.	2.5	11
15	Improvement of the conversion efficiency of as-deposited Bi <sub>2</sub> S <sub>3</sub> /PbS solar cells using a CeO <sub>2</sub> buffer layer. Thin Solid Films, 2019, 670, 93-98.	1.8	18
16	Raman effect in multiferroic Bi <sub>5</sub> Fe <sub>1+x</sub> Ti <sub>3</sub> â€“O <sub>15</sub> solid solutions: A temperature study. Journal of Applied Physics, 2018, 123, .	2.5	9
17	Detection of Clavibacter michiganensis subsp. michiganensis Assisted by Micro-Raman Spectroscopy under Laboratory Conditions. Plant Pathology Journal, 2018, 34, 381-392.	1.7	8
18	Deformation behavior of titanate nanotubes subjected to high pressure. Journal of Applied Physics, 2017, 121, 025902.	2.5	5

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19	Raman spectra of single walled carbon nanotubes at high temperatures: pretreating samples in a nitrogen atmosphere improves their thermal stability in air. <i>Physical Chemistry Chemical Physics</i> , 2017, 19, 7215-7227.	2.8	12
20	Complex refractive index of In <sub>x</sub> Ga <sub>1-x</sub> N thin films grown on cubic (100) GaN/MgO. <i>Thin Solid Films</i> , 2017, 626, 55-59.	1.8	6
21	Growth of HfO <sub>2</sub> /TiO <sub>2</sub> nanolaminates by atomic layer deposition and HfO <sub>2</sub> -TiO <sub>2</sub> by atomic partial layer deposition. <i>Journal of Applied Physics</i> , 2017, 121, .	2.5	46
22	Raman spectroscopy mapping of Si (001) surface strain induced by Ni patterned micro arrays. <i>Journal of Applied Physics</i> , 2017, 122, 125703.	2.5	0
23	Bending stability of GaN grown on a metallic flexible substrate by plasma-assisted molecular beam epitaxy. <i>Materials Research Express</i> , 2017, 4, 085903.	1.6	1
24	Evolutionary Algorithm Geometry Optimization of Optical Antennas. <i>International Journal of Antennas and Propagation</i> , 2016, 2016, 1-7.	1.2	6
25	Structural characterization of AlGaAs:Si/GaAs (631) heterostructures as a function of As pressure. <i>Journal of Vacuum Science and Technology B: Nanotechnology and Microelectronics</i> , 2016, 34, 02L119.	1.2	2
26	Chemical and surface analysis during evolution of arsenopyrite oxidation by <i>Acidithiobacillus thiooxidans</i> in the presence and absence of supplementary arsenic. <i>Science of the Total Environment</i> , 2016, 566-567, 1106-1119.	8.0	24
27	Tuning emission in violet, blue, green and red in cubic GaN/InGaN/GaN quantum wells. <i>Journal of Crystal Growth</i> , 2016, 435, 110-113.	1.5	10
28	Bulk lattice parameter and band gap of cubic In <sub>x</sub> Ga <sub>1-x</sub> N (001) alloys on MgO (100) substrates. <i>Journal of Crystal Growth</i> , 2015, 418, 120-125.	1.5	24
29	Determination of the Thermal Expansion Coefficient of Single-Wall Carbon Nanotubes by Raman Spectroscopy. <i>Spectroscopy Letters</i> , 2015, 48, 139-143.	1.0	8
30	Structural and Optical Properties of Ge <sub>1-x</sub> Sn <sub>x</sub> Alloys Grown on GaAs (001) by R. F. Magnetron Sputtering. <i>ECS Transactions</i> , 2014, 64, 393-400.	0.5	0
31	High-quality InN films on MgO (100) substrates: The key role of 30° in-plane rotation. <i>Applied Physics Letters</i> , 2014, 104, 191904.	3.3	2
32	Polarized Raman spectroscopy of corrugated MBE grown GaAs (6̄1,3̄1,1̄1,) homoepitaxial films. <i>Journal of Crystal Growth</i> , 2013, 378, 105-108.	1.5	2
33	Ge <sub>1-x</sub> Sn <sub>x</sub> Alloys Pseudomorphically Grown on Ge (001) by Sputtering. <i>ECS Transactions</i> , 2013, 50, 413-417.	0.5	0
34	Allometric Pressure versus Volume Behavior of Single-Walled Carbon Nanotubes Under High Pressure. <i>Advanced Science, Engineering and Medicine</i> , 2013, 5, 262-265.	0.3	2
35	Self-Assembly of In <sub>2</sub> GaN/MgO Nanobars. <i>Advanced Science Letters</i> , 2012, 16, 229-236.	0.2	0
36	Effect of oxygen incorporation on the vibrational properties of Al <sub>0.2</sub> Ga <sub>0.3</sub> In <sub>0.5</sub> P:Be films. <i>Thin Solid Films</i> , 2011, 520, 53-56.	1.8	2

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37	Interfacial insights of pyrite colonized by Acidithiobacillus thiooxidans cells under acidic conditions. Hydrometallurgy, 2010, 103, 35-44.	4.3	19
38	Infrared study of the absorption edge of $\hat{I}^2$ -InN films grown on GaN/MgO structures. Journal of Applied Physics, 2010, 108, .	2.5	4
39	Critical thickness of $\hat{I}^2$ -InN/GaN/MgO structures. Journal of Applied Physics, 2010, 107, 083510.	2.5	11
40	Study of the effect of DMSO concentration on the thickness of the PSS insulating barrier in PEDOT:PSS thin films. Synthetic Metals, 2010, 160, 1501-1506.	3.9	128
41	Infrared reflectance anisotropy of wurzite GaN. Journal of Applied Physics, 2009, 106, 063523.	2.5	0
42	In situ measurements of the critical thickness for strain relaxation in $\hat{I}^2$ -GaN/MgO structures. Journal of Crystal Growth, 2009, 311, 1302-1305.	1.5	8
43	Low energy shifted photoluminescence of Er <sup>3+</sup> incorporated in amorphous hydrogenated silicon-germanium alloys. Journal of Non-Crystalline Solids, 2009, 355, 976-981.	3.1	1
44	Dependence on the growth direction of the strain in AlGaSb alloys. Journal of Physics: Conference Series, 2009, 167, 012044.	0.4	3
45	Controlling the dimensions, reactivity and crystallinity of multiwalled carbon nanotubes using low ethanol concentrations. Chemical Physics Letters, 2008, 453, 55-61.	2.6	66
46	Raman and FTIR Spectroscopy of GaSb and Al <sub>x</sub> Ga <sub>1-x</sub> Sb Alloys with Nanometric Thickness Grown at Low Temperatures by Liquid Phase Epitaxy. AIP Conference Proceedings, 2008, , .	0.4	1
47	Nonlinear behavior of the energy gap in Ge <sub>1-x</sub> Sn <sub>x</sub> alloys at 4K. Applied Physics Letters, 2007, 91, .	3.3	43
48	Study of the GaAs MBE growth on (631)-oriented substrates by Raman spectroscopy. Journal of Crystal Growth, 2007, 301-302, 884-888.	1.5	3
49	P-cracker cell temperature effects on the optical properties of AlGaInP:Be layers grown by SSMBE. Journal of Crystal Growth, 2007, 301-302, 84-87.	1.5	2
50	In-plane and out-of-plane lattice parameters of [11n] epitaxial strained layers. Journal of Crystal Growth, 2006, 291, 340-347.	1.5	10
51	Reducibility, heats of re-oxidation, and structure of vanadia supported on TiO <sub>2</sub> and TiO <sub>2</sub> -Al <sub>2</sub> O <sub>3</sub> supports used as vanadium traps in FCC. Thermochemica Acta, 2005, 434, 74-80.	2.7	11
52	Quantum Hall effect devices based on AlGaAs/GaAs structures studied by photoreflectance spectroscopy. Applied Surface Science, 2004, 238, 204-208.	6.1	3
53	Determination of the optical energy gap of Ge <sub>1-x</sub> Sn <sub>x</sub> alloys with 0<x<0.14. Applied Physics Letters, 2004, 84, 4532-4534.	3.3	83
54	Giant reflectance anisotropy of polar cubic semiconductors in the far infrared. Physica Status Solidi C: Current Topics in Solid State Physics, 2003, 0, 2982-2986.	0.8	3

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55	Study of internal electric fields in AlGaAs/GaAs two-dimensional electron gas heterostructures. Microelectronics Journal, 2003, 34, 521-523.	2.0	5
56	Ge <sub>1-x</sub> Sn <sub>x</sub> alloys pseudomorphically grown on Ge(001). Applied Physics Letters, 2003, 83, 4942-4944.	3.3	45
57	Structural characterization of semi-strained layer (GaAs) <sub>1-x</sub> (Si <sub>2</sub> ) <sub>x</sub> /GaAs multilayers grown by magnetron sputtering. Thin Solid Films, 2002, 416, 49-53.	1.8	0
58	Growth of strained-layer GaAs/Ge superlattices by magnetron sputtering: Optical and structural characterization. Journal of Applied Physics, 2001, 89, 3209-3214.	2.5	4
59	Raman scattering study of (GaAs) <sub>1-x</sub> (Si <sub>2</sub> ) <sub>x</sub> alloys epitaxially grown on GaAs. Journal of Applied Physics, 2001, 90, 4977-4980.	2.5	6
60	Physical properties of (GaAs) <sub>1-x</sub> (Ge <sub>2</sub> ) <sub>x</sub> : Influence of growth direction. Physical Review B, 2001, 63, .	3.2	11
61	Influence of growth direction on order-disorder transition in (GaAs) <sub>1-x</sub> (Si <sub>2</sub> ) <sub>x</sub> alloys. Physical Review B, 2001, 65, .	3.2	3
62	Long-range order-disorder transition in (GaAs) <sub>1-x</sub> (Ge <sub>2</sub> ) <sub>x</sub> grown on GaAs(001) and GaAs(111). Microelectronics Journal, 2000, 31, 439-441.	2.0	5
63	Influence of growth direction on order-disorder transition in (GaAs) <sub>1-x</sub> (Ge <sub>2</sub> ) <sub>x</sub> semiconductor alloys. Applied Physics Letters, 2000, 77, 2497-2499.	3.3	10